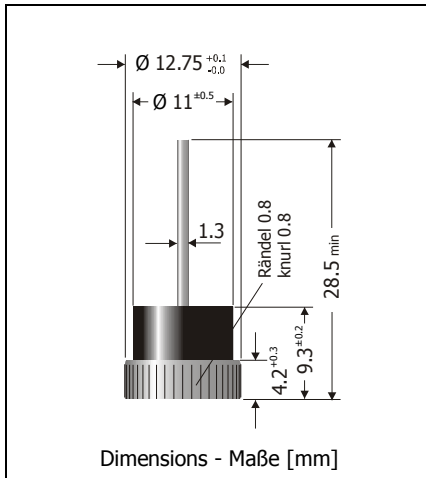


BYP60A05 ... BYP60A6, BYP60K05 ... BYP60K6

**Silicon-Press-Fit-Diodes – High Temperature Diodes
Silizium-Einpress-Dioden – Hochtemperatur-Dioden**

Version 2014-08-18



Nominal Current 60 A
 Nennstrom

Repetitive peak reverse voltage 50 ... 600 V
 Periodische Spitzensperrspannung

Metal press-fit case with plastic cover
 Metall-Einpressgehäuse mit Plastik-Abdeckung

Weight approx. 10 g
 Gewicht ca.

Compound has classification UL94V-0
 Vergussmasse nach UL94V-0 klassifiziert

Standard packaging: bulk
 Standard Lieferform: lose im Karton



Maximum ratings

Grenzwerte

Type / Typ Wire to / Draht an		Repetive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V]	Surge peak reverse voltage Stoßspitzensperrspannung V_{RSM} [V]
Anode	Cathode		
BYP60A05	BYP60K05	50	60
BYP60A1	BYP60K1	100	120
BYP60A2	BYP60K2	200	240
BYP60A3	BYP60K3	300	360
BYP60A4	BYP60K4	400	480
BYP60A6	BYP60K6	600	700
Max. average forward rectified current, R-load Dauergrenzstrom in Einwegschtung mit R-Last		$T_C = 150^\circ\text{C}$	I_{FAV} 60 A
Repetitive peak forward current Periodischer Spitzenstrom		$f > 15\text{ Hz}$	I_{FRM} 190 A ¹⁾
Peak forward surge current, 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwell		$T_A = 25^\circ\text{C}$	I_{FSM} 450/500 A
Rating for fusing, $t < 10\text{ ms}$ Grenzlastintegral, $t < 10\text{ ms}$		$T_A = 25^\circ\text{C}$	i^2t 1000 A²s
Operating junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur			T_j -50...+215°C T_s -50...+215°C

1 Max. case temperature $T_C = 150^\circ\text{C}$ – Max. Gehäusetemperatur $T_C = 150^\circ\text{C}$

Characteristics

Kennwerte

Forward Voltage – Durchlass-Spannung	$T_j = 25^\circ\text{C}$ $I_F = 60\text{ A}$	V_F	< 1.1 V
Leakage Current – Sperrstrom	$T_j = 25^\circ\text{C}$ $V_R = V_{RRM}$	I_R	< 100 μA
Thermal Resistance Junction – Case Wärmewiderstand Sperrschicht – Gehäuse		R_{thC}	< 0.6 K/W
Maximum pressing force Maximaler Einpressdruck		F_{pmax}	4 kN

